



- Notes:**
1. All dimensions in millimeters
 2. An epoxy meniscus may extend 1.5mm(0.059") down leads
 3. Tolerances unless dimensions ±0.25mm

AND-T4C-4N

InGaN Ultra Bright White Power LED

Features

- High Flux Output
- Low Profile
- Low Thermal Resistance
- Low Power Consumption
- The phosphor filled in the reflector converts the blue emission of InGaN chip to ideal white
- The product itself will remain within RoHS compliant versions
- Wide viewing angles 60°
- Typical chromaticity coordinates x=0.29, y=0.30
- ESD-withstand voltage: up to 4KV

Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Rating	Units
Continuous Forward Current	I _F	30	mA
Peak Forward Current	I _{FP}	100	mA
Reverse Voltage	V _R	5	V
Operating Temperature	T _{opr}	-40 ~ +85	°C
Storage Temperature	T _{stg}	-40 ~ +100	°C
Soldering Temperature(T=5 sec)	T _{sol}	260 ± 5	°C
Power Dissipation	P _d	100	mW
Zener Reverse Current	I _z	100	mA
Electrostatic Discharge	ESD	4000	V

Electro-Optical Characteristics (T_a = 25°C)

Parameter	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F = 30 mA	—	3.6	4.0	V
Reverse Current	I _R	V _R = 5 V	—	—	10	mA
Total Flux	Φ _V	I _F = 30 mA	2250	3600	—	mlm
Viewing Angle	2θ 1/2	I _F = 30 mA	—	60	—	deg
Chromaticity Coordinates	x	I _F =30mA	—	0.29	—	—
	y		—	0.30	—	
Zener Reverse Voltage	V _z	I _F = 20 mA	5.8	—	—	V

Luminous Intensity (mlm at 30mA)

Rank	Min	Max
N	2250	2850
P	2850	3600
Q	3600	4500

*Luminous Intensity: ±15%

Forward Voltage (V at 30mA)

Group	B				
Rank	1	2	3	4	5
Min	3.00	3.20	3.40	3.60	3.80
Max	3.20	3.40	3.60	3.80	4.00

* Forward Voltage: ±0.1V

